Silicon PNP Power Transistors 2SB1273

DESCRIPTION

·With TO-220 package

·Low collector saturation voltage

APPLICATIONS

·Designed for use in low frequency power amplifier applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

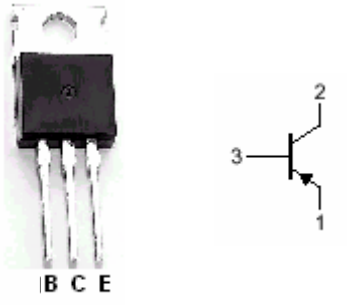


Fig.1 simplified outline (TO-220) and symbol

Absolute maximum ratings(Ta=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-60	V
V_{CEO}	Collector-emitter voltage	Open base	-60	V
V_{EBO}	Emitter-base voltage	Open collector	-6	V
I_C	Collector current		-3	A
I_{CM}	Collector current-peak		-8	A
P_C	Collector power dissipation	T_C=25□	30	W
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-55~150	□

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=-5mA ,R_{BE}=∞	-60			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	I_C=-1mA ,I_E=0	-60			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E=-1mA ,I_C=0	-6			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=-2A; I_B=-0.2A		-0.4	-1.0	V
V_{BE}	Base-emitter on voltage	I_C=-0.5A ; V_{CE}=-5V		-0.8	-1.0	V
I_{CBO}	Collector cut-off current	V_{CB}=-40V; I_E=0			-100	μA
I_{EBO}	Emitter cut-off current	V_{EB}=-4V; I_C=0			-100	μA
h_{FE-1}	DC current gain	I_C=-0.5A ; V_{CE}=-5V	70		280	
h_{FE-2}	DC current gain	I_C=-3A ; V_{CE}=-5V	20			
C_{OB}	Output capacitance	I_E=0 ; V_{CB}=-10V,f=1MHz		60		pF
f_T	Transition frequency	I_C=-0.5A ; V_{CE}=-5V		100		MHz

◆ **h_{FE-1} Classifications**

Q	R	S
70-140	100-200	140-280

PACKAGE OUTLINE

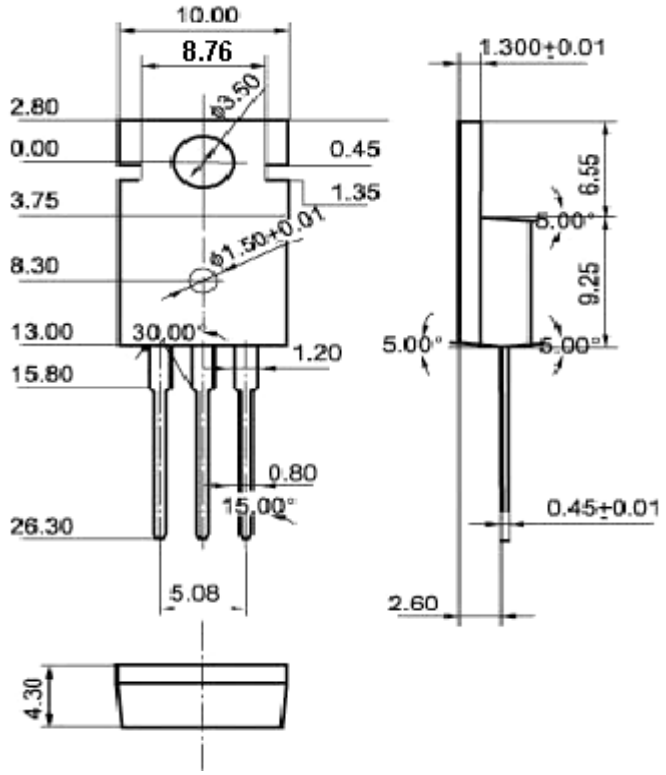


Fig.2 Outline dimensions(unindicated tolerance:±0.10 mm)